

Small switching (60V, 2A)

2SK2463

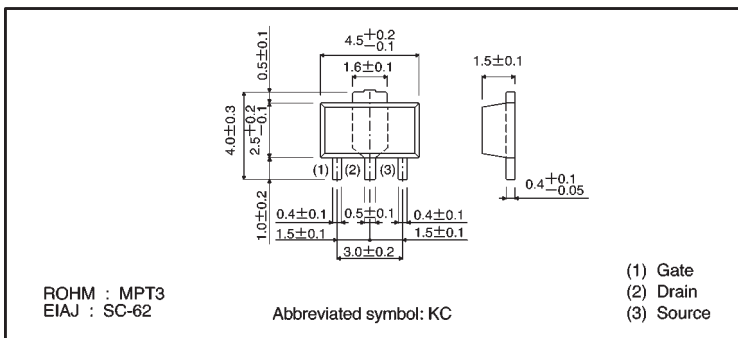
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Low-voltage drive (4V).
- 5) Easily designed drive circuits.
- 6) Easy to parallel.

●Structure

Silicon N-channel
MOSFET

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	60	V
Gate-source voltage		V _{GSS}	±20	V
Drain current	Continuous	I _D	2	A
	Pulsed	I _{DP} *1	8	A
Reverse drain current	Continuous	I _{DR}	2	A
	Pulsed	I _{DRP} *1	8	A
Total power dissipation		P _D	0.5 2*2	W
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	−55~+150	°C

*1 $P_w \leq 10 \mu s$, Duty cycle $\leq 1\%$ *2 When mounted on a 40 × 40 × 0.7 mm alumina board.

●Packaging specifications

Type	Package	Taping
	Code	T100
	Basic ordering unit (pieces)	1000
2SK2463		○

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-source leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	—	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}$	—	0.30	0.38	Ω	$I_D = 1A, V_{GS} = 10V$
		—	0.45	0.58		$I_D = 1A, V_{GS} = 4V$
Forward transfer admittance	$ Y_{fs} ^*$	1.2	—	—	S	$I_D = 1A, V_{DS} = 10V$
Input capacitance	C_{iss}	—	200	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	80	—	pF	$V_{GS} = 0V$
Reverse transfer capacitance	C_{rss}	—	50	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = 1A, V_{DD} \approx 30V$
Rise time	t_r	—	25	—	ns	$V_{GS} = 10V$
Turn-off delay time	$t_{d(off)}$	—	50	—	ns	$R_L = 30\Omega$
Fall time	t_f	—	50	—	ns	$R_G = 10\Omega$
Reverse recovery time	t_{rr}	—	70	—	ns	$I_{DR} = 2A, V_{GS} = 0V, di/dt = 50A/\mu s$

* $P \leq 300 \mu s$, Duty cycle $\leq 1\%$

●Electrical characteristic curves

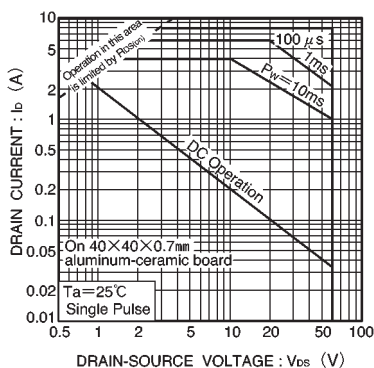


Fig.1 Maximum safe operating area

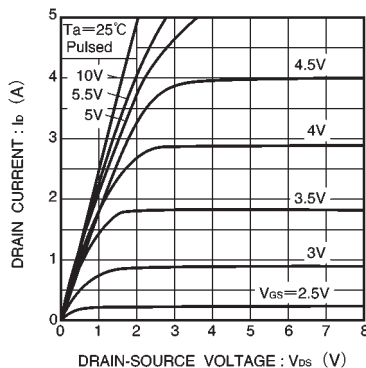


Fig.2 Typical output characteristics

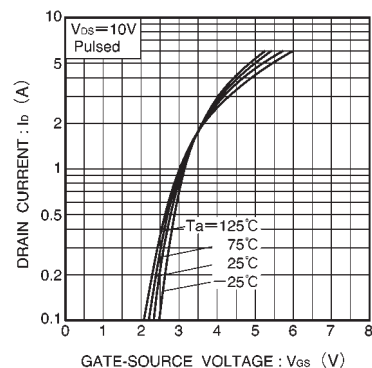


Fig.3 Typical transfer characteristics

● Electrical characteristic curves

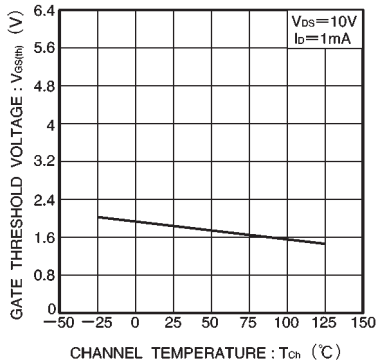


Fig.4 Gate threshold voltage vs. channel temperature

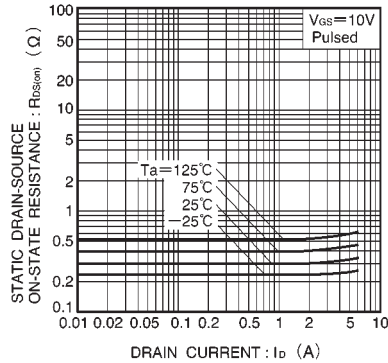


Fig.5 Static drain-source on-state resistance vs. drain current (I)

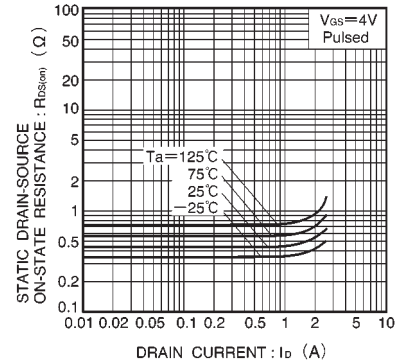


Fig.6 Static drain-source on-state resistance vs. drain current (II)

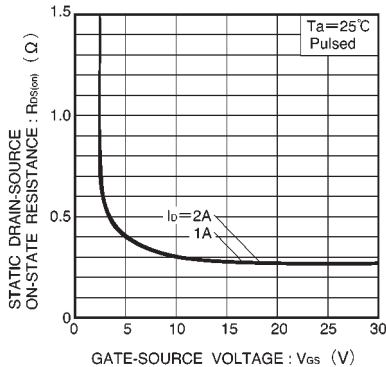


Fig.7 Static drain-source on-state resistance vs. gate-source voltage

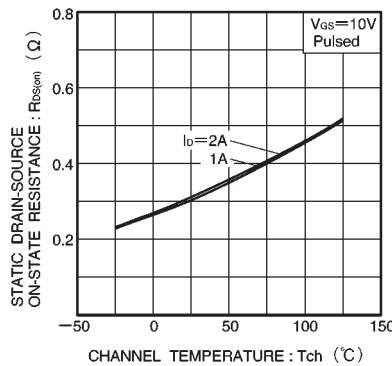


Fig.8 Static drain-source on-state resistance vs. channel temperature

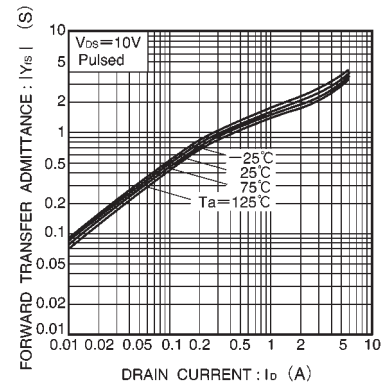


Fig.9 Forward transfer admittance vs. drain current

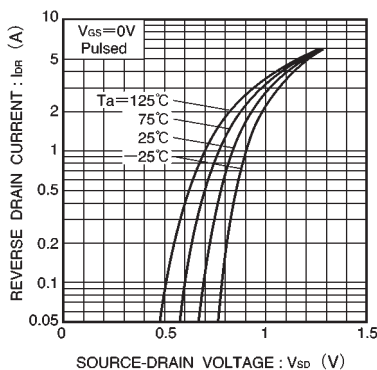


Fig.10 Reverse drain current vs. source-drain voltage (I)

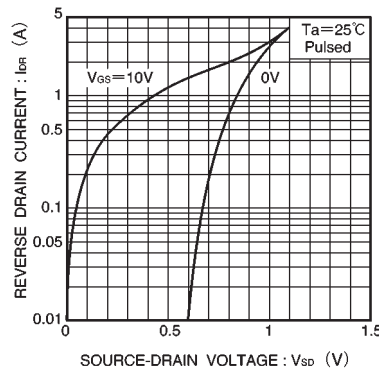


Fig.11 Reverse drain current vs. source-drain voltage (II)

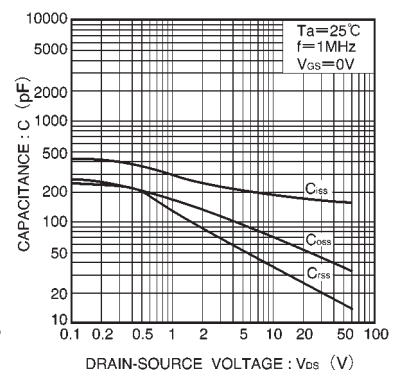


Fig.12 Typical capacitance vs. drain-source voltage

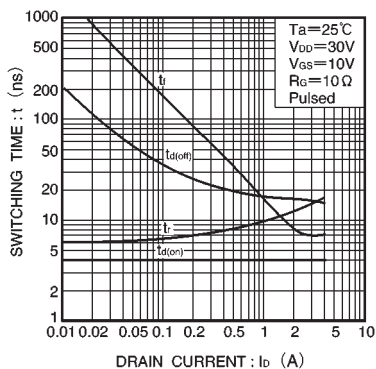


Fig.13 Switching characteristics
(See Figures 16 and 17 for
the measurement circuit and
resultant waveforms)

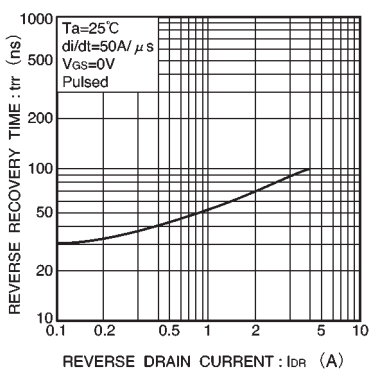


Fig.14 Reverse recovery time
vs. reverse drain current

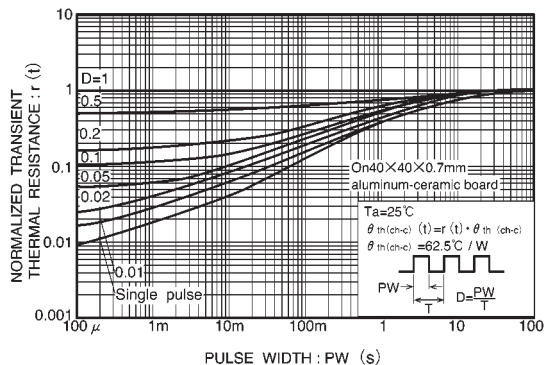


Fig.15 Normalized transient thermal
resistance vs. pulse width

● Switching characteristics measurement circuit

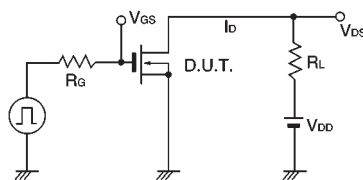


Fig.16 Switching time measurement circuit

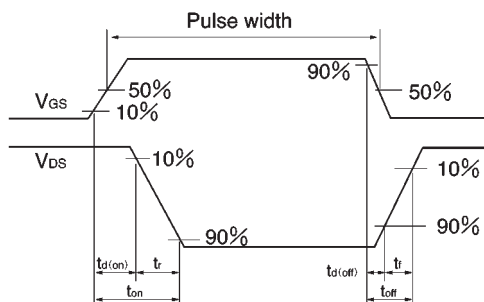


Fig.17 Switching time waveforms